ABSTRACT

An inventive semiconductor device is provided with: a silicon carbide substrate **1**; an n-type high resistance layer **2**; well regions **3** provided in a surface region of the high resistance layer **2**; a p^+ contact region **4** provided within each well region **3**; a source region **5** provided to laterally surround the p^+ contact region **4** within each well region **3**; first source electrodes **8** provided on the source regions **5** and made of nickel; second source electrodes **9** that cover the first source electrodes **8** and that are made of aluminum; a gate insulating film **6** provided on a portion of the high resistance layer **2** sandwiched between the two well regions **3**; a gate electrode **10** made of aluminum; and an interlayer dielectric film **11** that covers the second source electrodes **9** and the gate electrode **10** and that is made of silicon oxide.